

# PROCEEDINGS OF SPIE

## ***Photomask and Next-Generation Lithography Mask Technology XVII***

**Kunihiro Hosono**

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Invited Papers Session

**Kunihiro Hosono**, Renesas Technology Corporation (Japan)  
**John Lin**, Taiwan Semiconductor Manufacturing Company, Ltd.  
(Taiwan)

EUV Mask I

**Hiroshi Mohri**, Dai Nippon Printing Company, Ltd. (Japan)  
**Osamu Suga**, Semiconductor Leading Edge Technologies, Inc.  
(Japan)  
**Banqive Wu**, Applied Materials, Inc. (United States)

EUV Mask II

**Osamu Suga**, Semiconductor Leading Edge Technologies, Inc.

(Japan)

**Hiroshi Mohri**, Dai Nippon Printing Company, Ltd. (Japan)

**Banqie Wu**, Applied Materials, Inc. (United States)

Nano Imprint and Patterned Media

**Morihsa Houga**, Dai Nippon Printing Company, Ltd. (Japan)

**Youichi Usui**, HOYA Corporation (Japan)

Material and Process

**Toshio Konishi**, Toppan Printing Company, Ltd. (Japan)

**Koji Murano**, Toshiba Corporation (Japan)

**Thomas B. Faure**, IBM Corporation (United States)

Process and Repair

**Toshio Konishi**, Toppan Printing Company, Ltd. (Japan)

**Koji Murano**, Toshiba Corporation (Japan)

**Thomas B. Faure**, IBM Corporation (United States)

Pattern Generation

**Noriaki Nakayamada**, NuFlare Technology, Inc. (Japan)

**Jeff Farnsworth**, Intel Corporation (United States)

Metrology and Inspection

**Tatsuya Tomita**, Dai Nippon Printing Company, Ltd. (Japan)

**Shinji Akima**, Toppan Printing Company, Ltd. (Japan)

**Byung Gook Kim**, SAMSUNG Electronics Company, Ltd.

(Korea, Republic of)

Mask-related Lithography

**Minoru Sugawara**, Sony Corporation (Japan)

**Steffen Schulze**, Mentor Graphics Corporation (United States)

EDA, DFM, and MDP

**Kokoro Kato**, SII NanoTechnology Inc. (Japan)

**Nobuyuki Nishiguchi**, Semiconductor Technology Academic Research Center (Japan)